

## **REMARKS**

Claims 1 through 20 are pending in this application. Claims 3-6, 11, 12, 15, 16 and 20 are amended in several particulars for purposes of clarity in accordance with current Office policy, to assist the examiner and to expedite compact prosecution of this application. The Applicant appreciates the Examiner's indication of allowability concerning claims of claims 3, 5, and 15.

### **I. Election/Restriction**

The Examiner maintains the restriction requirement. However, the Applicant states again that there is no serious burden on the Examiner under MPEP § 803 because the non-elected claims all depend on the elected claims and thus necessitates a search of all the relevant areas for the non-elected claims as well as the elected claims.

### **II. Specification**

The Examiner stated that the title of the invention is not descriptive and that a new title is required that is clearly indicative of the invention to which the claims are directed.

Therefore, the title has been amended accordingly.

### **III. Claim Rejections - 35 USC § 112**

The Examiner stated that Claims 3-6, 15, and 16 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claims 3-6, 15 and 16 were amended to correct for antecedent basis.

#### IV. Claim Rejections - 35 USC § 102

Claims 1, 2, 4, 6, 13, 14, and 16 are rejected under 35 U.S.C. 102(b) as being anticipated by BUSTA (4,949,141). The Applicant respectfully traverses.

A. With regard to claims 1, 2, 4, and 6 the Examiner stated:

Busta discloses a thin film transistor comprising a buffer layer 12-32 formed on a substrate 10; an 8000 angstrom thick (Note column 5 line 9. The thickness of the activation layer 34 must be known to know whether the reference meets the claims) activation layer 34 formed on said buffer layer 12-32; and a gate insulation layer 40 having a thickness of at least 1,000 angstroms (1200-2000 angstroms, see column 5 line 20) formed on said substrate 10 including said activation layer 34, with said buffer layer 12-32 having a 750 angstrom (column 5 line 9 discloses a 500-1500 angstrom range) step 32 (the size of the step 32 is defined by projecting buffer layer part 32. The projecting part and the step 32 it creates will be interchangeably referred to as part "32") formed between a lower part of said activation layer 34 and a part except said lower part of said activation layer 34, said 750 angstrom step 32 being a half or less of the thickness sum (the sum, of 8000, activation layer 34, and 1000, gate insulation layer 40, being 9000) of said activation layer 34 and gate insulation layer 40, and further comprising a 500 (500-1500 angstroms, note column 5 line 9) angstrom polysilicon layer 36. Note (figure 2B) that the thickness of the gate insulation layer 40 is not changed on said sidewall of said buffer layer 12-32 (the side wall of the buffer layer 12-32 is the sidewall of the step 32 portion of the buffer layer 12-32). Therefore the buffer layer 12-32 must have a step 32 to such a degree as to accomplish this visible result. Note figure 2B, column 4 lines 50-51, and column 5 lines 9,10, and 20 of Busta.

However, reference 32 which the Examiner is classifying as the buffer layer, is actually the drain layer according to col. 4, lines 49-68. Moreover, the Examiner only states that reference 34 is the activation layer. Looking at Busta, shows that 34 is a-n+Si:H layer and so is reference 36 and 38 serves as the source. Therefore, reference 32 can be included as the activation layer rather than

the buffer layer as the buffer layer is stated in the claim as not being the activation layer. Therefore, the height of the drain area is not pertinent to the comparison as mentioned in the claim.

B. With regard to claims 13,14, and 16, the Examiner stated that Busta discloses a thin film transistor comprising a buffer layer 12-32; an 8000 angstrom thick (Note column 5 line 9, activation layer 34 formed on said buffer layer 12-32; and a gate insulation layer 40 having a thickness of at least 1,000 angstroms (1200-2000 angstroms, see column 5 line 20) formed on said buffer layer 12-32 and said activation layer 34, with said buffer layer 12-32 having a 750 angstrom (column 5 line 9 discloses a 500-1500 angstrom range) step 32 (the size of the step 32 is defined by projecting buffer layer 12-32 part 32.

However, layer 32 is the drain layer which can still be categorized as the activation layer and not the buffer layer. Therefore, the step is not up to half of the thickness of the sum of the activation layer and the gate insulation layer.

#### Allowable Subject Matter

The Examiner stated that claims 3, 5, and 15 would be allowable if rewritten to overcome the rejection(s) under 35 U.S.C. 112 set forth in this Office action and to include all of the limitations of the base claim and any intervening claims.

The applicant appreciates the examiner's indication of allowability pertaining to claims 3, 5 and 15. In accordance with 37 C.F.R. § 1.111(b), the applicant respectfully requests that the

examiner temporarily hold objections and requirements as to form in abeyance until the remarks and amendments in this Amendment are considered by the examiner.

In view of the foregoing amendments and remarks, all claims are deemed to be allowable and this application is believed to be in condition to be passed to issue. If there are any questions, the examiner is asked to contact the applicant's attorney.

A fee of \$120.00 is incurred by filing a petition for one (1) month extension of time. Applicant's check drawn to the order of the Commissioner accompanies this Amendment. Should there be a deficiency in payment, or should other fees be incurred, the Commissioner is authorized to charge Deposit Account No. 02-4943 of Applicant's undersigned attorney in the amount of such fees.

Respectfully submitted,



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